

B. Amendment to the Specification

Please replace the specification with the enclosed substitute specification.

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- 1 -

**PIEZOELECTRIC FILM TYPE ACTUATOR,
LIQUID DISCHARGE HEAD,
AND METHOD OF MANUFACTURING THE SAME**

BACKGROUND OF THE INVENTION

Field of the Invention

[0001] The present invention relates to a piezoelectric film type actuator used for a liquid discharge head, a sound generating device, such as a microphone, a speaker, various kinds of vibrators or oscillators, as well as a sensor or the like, and also, relates to the method of manufacturing the same. Further, the invention relates to a liquid discharge head that uses the piezoelectric film type actuator, and the method of manufacture therefor. In this respect, the piezoelectric film type actuator referred to in the subject specification is a member that converts electric energy to mechanical energy such as to effectuate mechanical displacements, vibrations, or stresses. Also, it is a member that reverses such a conversion.

Related Background Art

[0002] In recent years, there has been a demand for a displacement element for adjusting the length and the position of optical path on a sub-micron order or a sensing element for detecting micro displacements as electrical changes in the fields of optics and precision processing. To meet this demand, there has been in progress a development of a piezoelectric film type actuator, which is a member that utilizes the displacement or the inverse phenomenon thereof based on the

reverse piezoelectric effect or electric distortion when an electric field is applied to the piezoelectric or electrically distortional material of a ferroelectric element.

[0003] Also, conventionally, it has been preferred to adopt the unimorph type or the bimorph type for the formation of a piezoelectric film type actuator used for the liquid discharge recording head or the like. In this respect, for the liquid discharge recording apparatus that uses a piezoelectric film type actuator of the kind for the enhancement of the printing quality and the printing speed, among some others, in order to meet such demand, the development has been in progress for the implementation to make the piezoelectric film type actuator smaller at a higher density, which can be driven at a lower voltage, but with a higher response performance, as well as for the provision of an elongated multiple nozzle.

[0004] Now, in order to obtain a large flexure displacement, a generating power, or a generation potential with the aforesaid unimorph- or bimorph-piezoelectric film type actuator, it is important to make the base plate that becomes the oscillating plate thinner. Here, however, the thickness of such a base plate is decreased and the strength thereof is reduced, leading to the problem that the smoothness is eventually reduced. Further, there is a problem for the conventional unimorph- or bimorph-piezoelectric film type actuator that the reliability thereof is marred due to the use of a bonding agent.

[0005] To overcome these problems, it is disclosed in the specification of Japanese Patent Application Laid-Open No. 62-213399 an increased bonding strength is provided by sintering piezoelectric ceramics and ceramics oscillating plate at a time without using any bonding agent.

[0006] However, in this method, different materials are sintered at high temperature. As a result, the oscillating plate and the piezoelectric ceramics are shrunk themselves, making it difficult to adjust the dimensional precision in the order of a micron on a large area. For that matter, the highly reliable piezoelectric film type actuator having a large area, or the liquid discharge head, can hardly be obtained.

SUMMARY OF THE INVENTION

[0007] It is an object of the present invention to provide a highly reliable piezoelectric film type actuator that can be highly integrated, making it possible to obtain large displacements at a low driving voltage with a high response speed, and also, to provide a liquid discharge head that uses such a piezoelectric film type actuator, as well as to provide the method of manufacture for each of the above.

[0008] It is another object of the invention to obtain a method for manufacturing a piezoelectric film type actuator having a piezoelectric film and an oscillating plate structural member bonded thereto, which method comprises the steps of forming a piezoelectric film on an intermediate transfer member; bonding the piezoelectric film on the intermediate member and the oscillating plate structural member; and peeling off the intermediate transfer member from the piezoelectric film.

[0009] For the method of the present invention for manufacturing a piezoelectric film type actuator, it is preferable for the piezoelectric film to contain lead, titanium, and zirconium. Also, the piezoelectric film may be the one which is patterned.

[0010] For the method of the present invention for manufacturing a piezoelectric, it is preferable that in the step of bonding the piezoelectric film and the oscillating plate structural member, the piezoelectric film and the oscillating plate structural member are bonded by means of energized heating, low temperature heating, or energized contact under pressure through a single metal, an alloy, a metal oxide, a metal nitride, or a metallic compound. Also, it is preferable to make the surface roughness Ra of the piezoelectric film 0.01 μm to 2.5 μm . More preferably, it is made 0.02 μm to 1.0 μm .

[0011] For the method of the present invention for manufacturing a piezoelectric film type actuator, it is preferable that in the step of peeling off the intermediate transfer member from the piezoelectric film, the intermediate transfer member is peeled off by the irradiation of a laser beam, such as an excimer laser beam or an infrared laser beam, among some others, through the intermediate transfer member.

[0012] For the method of the present invention for manufacturing a piezoelectric film type actuator, it is preferable that in the step of peeling off an intermediate transfer member from a piezoelectric film, a fluid flux (water jet) is discharged between the intermediate transfer member and the piezoelectric film to peel off the intermediate transfer member. It is also preferable to form a porous layer having a concentration of 30% to 95% between the intermediate transfer member and the piezoelectric film.

[0013] It is still another object of the present invention to provide a method for manufacturing a liquid discharge head provided with a base plate portion having liquid discharge ports, liquid chambers connected with the liquid discharge ports, and a piezoelectric film type actuator formed by a piezoelectric film and an oscillating plate provided for a part of the liquid chambers, for discharging liquid from the liquid discharge ports by means of the flexural oscillation of the piezoelectric film type actuator, which comprises the steps of forming a

piezoelectric film on an intermediate transfer member; bonding the piezoelectric film on the intermediate member and the oscillating plate structural member; and peeling off the intermediate transfer member from the piezoelectric film.

[0014] The piezoelectric film type actuator of the present invention is characterized in that it is manufactured by the aforesaid method for manufacturing a piezoelectric film type actuator. Also, the liquid discharge head of the present invention is characterized in that it is manufactured by the aforesaid method for manufacturing a liquid discharge head.

[0015] In accordance with the present invention, the piezoelectric film is not formed directly on the oscillating plate structural member, but through the intermediate transfer member. The step of forming the piezoelectric film and that of bonding the piezoelectric film to the oscillating plate structural member are separated. The film formation process of the piezoelectric film and the manufacturing process of the actuator are functionally separated. A wide selection of material is made possible for the oscillating plate structural member as an actuator, hence obtaining an advantage to provide a film after adjusting the performance thereof arbitrarily as a piezoelectric film. Also, when the piezoelectric film and the oscillating plate structural member are bonded, it is possible to set the heating temperature at 500°C or less for bonding, and the surface roughness Ra of the piezoelectric film is defined to be 0.01 μm to 2.5 μm . Then, bonding is effectuated by means of energized heating, low heating, or energized contact under pressure through a metal, an alloy, a metal oxide, a metal nitride, or a metallic compound. The bonding strength and durability are thus enhanced without using a bonding agent to provide a highly reliable piezoelectric film type actuator.

[0016] Further, the intermediate transfer member can be peeled off easily mechanically or by the irradiation of a laser beam without damaging the piezoelectric film. As a result, the intermediate transfer member can be utilized again.

[0017] In this way, it becomes possible to obtain a piezoelectric film type actuator capable of providing a large area and high integration, as well as generating large power, with which a large displacement is obtainable at a low driving voltage with a high response speed. Further, it becomes possible to manufacture a highly reliable elongated liquid discharge head in high density, which is capable of obtaining a large displacement at a low driving voltage with a stable and high response.

BRIEF DESCRIPTION OF THE DRAWINGS

[0018] Figs. 1A, 1B, 1C and 1D are views that illustrate the main process of a method for manufacturing a piezoelectric film type actuator in accordance with the present invention.

[0019] Fig. 2A is a perspective view, which shows a liquid discharge head in accordance with the present invention. Fig. 2B is a cross-sectional view, which shows the liquid discharge head represented in Fig. 2A, taken along line 2B - 2B in Fig. 2A. Fig. 2C is an enlarged cross-sectional view, which shows the piezoelectric film type actuator of the liquid discharge head of the present invention.

[0020] Figs. 3A, 3B and 3C are views, which show the process of forming a piezoelectric film on an intermediate transfer member in accordance with the method for manufacturing a liquid discharge head embodying the present invention; Fig. 3A is a plan view showing the state of forming a resin pattern on an intermediate transfer member; Fig. 3B is a cross-sectional view taken along line 3B - 3B in Fig. 3A; and Fig. 3C is a cross-sectional view, which shows the state of burying a complex material layer and a piezoelectric film paste between a mold formed on the intermediate transfer member.

[0021] Fig. 4 is a perspective view, which shows the state of forming the piezoelectric film in an array by the process of forming the piezoelectric film on the intermediate transfer member in accordance with the method for manufacturing a liquid discharge head embodying the present invention.

[0022] Fig. 5 is a perspective view, which shows the structural member of an oscillating plate to be bonded to the piezoelectric film in the method for manufacturing a liquid discharge head embodying the present invention.

[0023] Fig. 6 is a cross-sectional view, which shows the process of bonding the piezoelectric film and the structural member of the oscillating plate in the method for manufacturing a liquid discharge head embodying the present invention.

[0024] Fig. 7 is a cross-sectional view, which shows the liquid discharge head manufactured by the method for manufacturing a liquid discharge head embodying the present invention.

[0025] Figs. 8A, 8B, 8C, 8D, 8E and 8F are views, which schematically illustrate the main process of the method for manufacturing a liquid discharge head in accordance with another embodiment of the present invention.

DETAILED DESCRIPTION OF THE PREFERRED EMBODIMENTS

[0026] Hereinafter, with reference to the accompanying drawings, the embodiments in accordance with the present invention will be described.

[0027] Figs. 1A to 1D are the views, which illustrate the main process of a method for manufacturing a piezoelectric film type actuator in accordance with the present invention.

[0028] The main process of the method of manufacture for the piezoelectric film type actuator (hereinafter referred to simply as an actuator) in accordance with the present invention consists of the process of forming a piezoelectric film on an intermediate transfer member, the process of bending the piezoelectric film on the intermediate transfer member to the structural member of an oscillating plate, and the process of peeling off the intermediate transfer member from the piezoelectric film as shown in Figs. 1A to 1D.

[0029] In the first process, that is, the process of forming the piezoelectric film on the intermediate transfer member, a porous layer 3 is formed on an intermediate transfer member 2 as shown in Fig. 1A. Then, piezoelectric film 1 is formed thereon.

[0030] For the formation of the piezoelectric film 1, it is possible to appropriately adopt the known method, such as sintering, sputtering, sol-gel, CVD, hydrothermal synthesis, laser ablation, or gas deposition, among some others, and select the piezoelectric film composition and the method of manufacture, which can provide characteristics fit for an intended use. As the composition of the piezoelectric film 1, there may be usable such composition as lead zirconia titanate (PZT), barium titanate, or barium zirconia titanate having the perovskite structure, which is an oxide composed of lead, titanium, and zirconium or a composition obtainable by adding Mn, Nb, La, Ge, or some other element to any one of them. As the crystallinity of the piezoelectric film, either a polycrystalline element or a single crystalline element may be usable. Also, as the mode of the piezoelectric film 1, a patterned mode is represented in Fig. 1A, but various modes may be employed depending on usage, and the mode is not necessarily limited to the patterned one. As the patterning method, there is the one that dry or wet etches a solid film, performs sand blasting or cutting process mechanically, or patterns after forming a metal mask or resist at the time of film formation. Further, there is a lift-off method where a highly precise mold is formed with a light hardening type resin, and a PZT paste is buried in-between. The film thickness of the piezoelectric film 1 is 0.1 μm to 20 μm , or preferably, 0.5 μm to 12 μm .

[0031] Also, as the intermediate transfer member 2 that forms the piezoelectric film 1, inorganic oxide, such as alumina, zirconia, magnesia, or sapphire, is used. Here, a single crystal may be used depending on usage. Also, it is preferable to set the film thickness of the intermediate transfer member 2 at 10 μm to 5 mm, or more preferably, 100 μm to 2 mm. If the film thickness of the intermediate transfer member 2 is less than 10 μm , a problem is encountered in that it becomes unfavorable to maintain the shape of the piezoelectric film 1, and also, in that it becomes difficult to handle the piezoelectric film for bonding at the next step. Also, it is not preferable to make the film thickness more than 5 mm, because there is then a problem in that the intermediate transfer member 2 cannot be peeled off easily without damaging the piezoelectric film 1 when peeled from the intermediate transfer member 2 after bonding. Also, on the intermediate transfer member 2, electrodes for actuator use can be formed in advance. Here, as described later, there may be the case where the optical property or the layer structure of the intermediate transfer member 2 is limited depending on the method of peeling in the peeling process subsequent to bonding.

[0032] The porous layer 3 is formed to make it easier to peel off the intermediate transfer member 2 after the piezoelectric film 1 is bonded to the oscillating plate structural member 4. It is preferable to form the porous layer 3 with a material containing carbon or non-sintering ceramics. For example, then, on the intermediate transfer member 2, a layer that contains carbon and metallic oxide is formed in advance, and the piezoelectric film 1 and the intermediate transfer member 2 are separated by breaking the brittle porous layer 3 when the layer that contains carbon becomes a brittle metal oxide layer due to heat from firing the piezoelectric film 1. In this way, the intermediate transfer member 2 can be peeled off easily. Here, as described later, depending on the peeling method, such as using the irradiation of laser beam, for example, it is possible to peel off the intermediate transfer member 2 without any intervention of the porous layer 3.

[0033] Also, the surface roughness R_a on the side of the piezoelectric film 1 where it is bonded to the oscillating plate structural member 4 should desirably be within a range of 0.01 μm to 2.5 μm . More preferably, it is within a range of 0.02 μm to 1.0 μm . It is preferable to keep the surface roughness R_a of the piezoelectric film 1 within the surface roughness R_a of the aforesaid range in order to enhance the durability of the actuator, while making it possible to bond the piezoelectric film 1 to the oscillating plate structural member 4 at lower temperature under lower pressure (see Fig. 1B). If the surface roughness R_a of the piezoelectric film 1 is less than 0.01 μm , the bounding strength becomes insufficient, and a problem may

be encountered in some cases in that the structure member 4 of the oscillating plate and the piezoelectric film 1 are peeled off in the peeling step in the following process. Also, it is not preferable to allow the surface roughness R_a of the piezoelectric film to exceed $2.5\text{ }\mu\text{m}$, because then the characteristics of the actuator (characteristics of its displacement and frequency) become defective. With the surface roughness R_a of the piezoelectric film 1 being kept within the range as described above, it becomes possible to obtain a good bonding strength, and a highly reliable actuator in particular. Also, the surface roughness R_{a1} of the oscillating plate 5 of the structural member 4 thereof, which is in contact with the piezoelectric film 1, should desirably be such as to make the difference of absolute values, $|R_{a1} - R_a|$, $0.5\text{ }\mu\text{m}$ or less with respect to the surface roughness R_a of the piezoelectric film 1. Here, the surface roughness can be measured by using a surface roughness meter "Surfcoder" manufactured by Kosaka Institute.

[0034] Now, in the second process, which is the step of bonding the piezoelectric film to the oscillating plate structural member, there is formed the oscillating plate structural member 4 with the oscillating plate 5 and the base plate portion 6 that constitute the actuator as shown in Fig. 1B. Here, the oscillating plate 5 and the base plate 6 may be formed integrally or bonded together. For the oscillating plate structural member 4, heat resistance is needed so that it is not deformed by heat when bonded to the piezoelectric film 1. It is preferable to use a material having a heat resistance of 150°C or more. In this respect, the heat resistance of 150°C or more means that the possible dimensional displacement is less than 3% after a heat treatment under an atmosphere at 150°C for a period of 30 minutes.

[0035] For the oscillating plate 5, a material having the Young's modulus of 50 GPa or more, such as SUS, Ti, zirconia, Si, Cu, SiO_2 , glass, or Cr, is usable. The oscillating plate 5 may be a one-layer structure or a plural-layer structure. Even in a case of the plural-layer structure, there is a need for providing the Young's modulus of 50 GPa or more as a whole. The film thickness of the oscillating plate 5 is $0.5\text{ }\mu\text{m}$ to $20\text{ }\mu\text{m}$. More preferably, it is $1\text{ }\mu\text{m}$ to $10\text{ }\mu\text{m}$. Also, for the oscillating plate 5, it may be possible to use the one which is doped with a minute amount of a metal, such as Y or B.

[0036] The material of the base plate 6 of the oscillating plate structural member 4 may be the same as the material of the oscillating plate 5, but a ceramics compound material that contains alumina, celcyan, magnesia, or carbon fiber may be useable as another material therefor. When the actuator is applied to a liquid discharge head, it may be possible to use a Si base plate or a SUS base plate for the base plate portion 6, for example, which is processed to have formed a liquid chamber in

advance or yet to be processed to provide a liquid chamber in the post process that may follow. The liquid chamber of the liquid discharge head can be formed by machining, etching, or the like.

[0037] Then, when the piezoelectric film 1 and the oscillating plate structural member 4 are bonded, a bonding layer 7 (or bonding layers 7a and 7b) of a metal, a metal alloy, a metal oxide, a metal nitride, or a metallic compound substance is filmed on both the surface of the piezoelectric film 1 and of the oscillating plate 5 to be bonded or on either one of these surfaces as shown in Fig. 1B. As the metal or alloy to be filmed on the surfaces of the oscillating plate structural member 14 and piezoelectric member 11 to form the bonding layers 7 (7a and 7b), a metal of at least one kind or more is usable among Pd, In, Sn, Ni, Ga, Cu, Ag, Mo, Ti, Zr or some other metal, and also, as the alloy, PdIn₃, Al-Cu, Ti-Ni, or the like is usable. As the metal oxide, there is SiO₂, CaO₂, TiO₂, ZnO, or the like, for example. As the metal nitride, there is TiN, Si₃N₄, or the like, for example. As the metallic compound substance, there is Ti-Ni, Ag-Ni, Fe-Co, Cr-Mo, or the like, for example. In this manner, on both surfaces or either one of the surfaces of the oscillating plate structural member 4 and the piezoelectric member 1, the bonding layer 7 (7a and 7b) is filmed, and after these members abut against each other, both of them are bonded by energized heating, energized contact under pressure, low-temperature heating, or the like.

[0038] Here, the energized heating used for bonding is a method of bonding by means of heat generated when current flows through a conductive layer. The quantity of current is 0.5 A/cm² to 200 A/cm² or preferably it is 1 A/cm² to 50 A/cm². The energized contact under pressure is a method of a still firmer bonding by exerting pressure in addition to the aforesaid energized heating method. Also, the low-temperature heating is a method of bonding by forming an alloy on the bonding surfaces with a combination of different kinds of metals that form alloys at a temperature of 300°C or less. Particularly, with a combination of Pd and In, it is possible to form an alloy of PdIn₃ at about 250°C. Therefore, this combination is preferable for a bonding at a lower temperature. Besides this combination, it is possible to bond by combining Ag-Ni, Ti-Ni, Zr-Cu, among some others.

[0039] The third process, which is a step of peeling off the piezoelectric film from the intermediate transfer member, is that, as shown in Fig. 1C, the intermediate transfer member 2 is cut off from the actuator, which is formed by bonding the piezoelectric film 1 and the oscillating plate structural member 4. As the technique used for peeling off the intermediate transfer member 2, there is one where a porous layer 3 is provided between the intermediate transfer member 2 and the

piezoelectric film 1, and this porous layer 3 is mechanically destroyed so as to peel off the intermediate transfer member 2. There is also the one where the intermediate transfer member 2 is destroyed by a water jet method so as to peel it off or to peel off the intermediate transfer member 2 by means of rapid heating by the irradiation of a laser beam. In this respect, no porous layer 3 may be required for the technique that employs the irradiation of a laser beam for peeling.

[0040] For the application of the former two techniques (mechanical peeling and peeling by the water jet method), it is preferable to form a porous layer 3 of 30% to 95% concentration or preferably that of 50% to 95% concentration on the interface between the piezoelectric film 1 and the intermediate transfer member 2 when the piezoelectric film 1 is formed. The film thickness of the porous layer 3 is 0.5 μm to 200 μm or preferably 1.0 μm to 100 μm . With regard to this porous layer 3, the ceramic oxide layer that contains carbon is produced in advance on the intermediate transfer member 2, for example, and a porous layer is formed on the interface by carbon, which is fired when the piezoelectric film 1 is fired at a high temperature, and then, this brittle porous layer is mechanically destroyed to easily peel off the piezoelectric film 1 from the intermediate transfer member 2. In this respect, the concentration of the porous layer can be determined with the measurement of the aperture area by observing the section of the porous layer using a TEM (Transparent Electronics Microscope).

[0041] Further, it is a preferable mode that conductivity is provided to the porous layer 3 to utilize it as the actuator electrodes. In such a case, a paste, which is prepared by the dispersion and mixture of metallic particles, carbon material, and ceramic particles in a solgel solution of SRO (strontium ruthenium oxide) or ITO, is coated to produce a film, thus obtaining a conductive porous layer.

[0042] Also, when the intermediate transfer member 2 is peeled off through the porous layer 3, it becomes easier to separate them with the collision of a highly pressurized fluid flux (water jet) with the porous layer 3. Generally, the water jet method is such as to cut or process ceramics, metal, resin, rubber, or woods, or perform a surface rinsing or the like by discharging a highly pressurized flux of water flow onto an object at high speed. As an example in which the water jet method is used, there are the following disclosures:

[0043] K. Ohmi et al. "Water Jet Splitting of Thin Porous Si for ELTRAN", The Japan Society of Applied Physics, Tokyo, pp. 345 to 355 (1999); and

[0044] R. Herino et al. "Microstructure of Porous Silicon and its Evaluation with Temperature", Mater. Lett. 2, pp. 519 to 523 (1984). In accordance with the present invention, the water jet is discharged to the porous layer 3 to selectively

collapse the porous layer 3 so as to enable the intermediate transfer member 2 to be separated. The pressure of the fluid used as the water jet is 5.0×10^4 kPa to 80.0×10^4 kPa or preferably, 10.0×10^4 to 50.0×10^4 kPa.

[0045] With regard to the technique of peeling off the intermediate transfer member by irradiating a laser beam, the piezoelectric film 1 is formed on the intermediate transfer member 2, and then, after an oscillating plate structural member 4 is bonded thereto, a laser beam is irradiated onto the piezoelectric film 1 from the opposite side of the oscillating plate 5 through the intermediate transfer member 2 for rapid heating, and by the difference in the instantaneous thermal expansion or thermal decomposition, the piezoelectric film 1 and the intermediate transfer member 2, which is a transparent base plate, are separated. As a laser beam, an excimer laser or an infrared laser can be used. When an excimer laser beam is applied, a material having a transmittance of 20% or more for light of 230 nm to 260 nm wavelength is used as the intermediate transfer member 2. Also, when an infrared laser beam is applied, a material having a transmittance of 20% or more for 700 nm to 1,250 nm is used as the intermediate transfer member. As the irradiating energy of the laser beam, it is preferable to apply 50 to 1,000 mJ/cm².

[0046] When an excimer laser beam is used for peeling, the intermediate transfer member 2 is sufficient if a material used therefor has a transmissivity of approximately 230 nm to 260 nm, while withstanding a temperature of 900°C or more at the time of firing the piezoelectric film array. Then, the intermediate transfer member functions sufficiently when this method is applied, and MgO substrate, alumina, sapphire, quartz glass, CaCO₃, LiF, or the like can be used, for example. Also, when peeling is effectuated by use of an infrared laser, such as a carbon gas laser or a YAG laser, the material, which presents a translucency of approximately 700 nm to 1,250 nm, while withstanding a temperature of 900°C or more at the time of firing the piezoelectric film array, can function sufficiently as the intermediate transfer member for this method, and MgO, MgF₂, Y₂O₃, CaF₂, quartz glass, alumina, sapphire, or SrTiO₃ single crystal substrate can be used, among some others.

[0047] In the processes described above, the piezoelectric film type actuator is formed with the piezoelectric film 1 and the oscillating plate structural member 4 being bonded as shown in Fig. 1D. Here, in Fig. 1D, a reference numeral 9 designates upper electrodes.

[0048] In the manufacture of the piezoelectric film type actuator as described above, the process to form the piezoelectric film 1 and the process to bond the piezoelectric film 1 to the oscillating plate structural member 4 are separated, and

the film formation process of the piezoelectric film 1 and the manufacturing process of the oscillating plate structural member are functionally separated. Therefore, there is a wide selection of materials that can be used for the oscillating plate structural member 4 serving as the actuator. Further, there is an advantage in that the film is obtainable after arbitrarily adjusting the performance of the piezoelectric film 1.

[0049] When the piezoelectric film and the oscillating plate structural member are bonded, the heating temperature can be set at as low as 500°C or less for bonding. Also, with the surface roughness Ra of the piezoelectric film being 0.01 μm to 2.5 μm, bonding is made by means of energized heating, low temperature heating, energized contact under pressure, or the like through a metal, an alloy, a metal oxide, a metal nitride, or a metallic compound without using any bonding agent. In this way, it becomes possible to enhance the bonding strength and durability, thus obtaining a highly reliable piezoelectric film type actuator. Further, the intermediate transfer member can be peeled off mechanically or by the irradiation of a laser through the porous layer easily without damaging the piezoelectric film. Also, the intermediate transfer member can be utilized again.

[0050] In this way, it becomes possible to obtain an element capable of obtaining a large displacement at a lower driving voltage with a large generating power at a faster response, which can also provide a large area for a higher integration arrangement. Thus, a highly reliable, large-area piezoelectric film type actuator can be manufactured, which can be preferably utilized for a sound generating device, such as a microphone, a speaker, various kinds of vibrators and oscillators, and various kinds of sensors, such as an acceleration sensor, a pressure sensor, a vibration sensor, an angular velocity sensor, in addition to a liquid discharge head.

[0051] Next, with reference to Figs. 2A, 2B and 2C to Figs. 8A, 8B, 8C, 8D, 8E and 8F, a liquid discharge head to be manufactured using the method for manufacturing the piezoelectric film type actuator of the present invention, and the method of manufacture thereof, will be described.

[0052] A liquid discharge head 11 of the present invention has a plurality of liquid discharge ports 12; the liquid chamber 13, which is installed for each of the liquid discharge ports 12; and each the piezoelectric films 14 arranged for each of the liquid chambers 13, respectively, as shown in Fig. 2A and Fig. 2B. Here, in Figs. 2A and 2B, the liquid discharge ports 12 are arranged on the lower end side, but these ports can be on the side end side.

[0053] For the liquid discharge head 11, the liquid discharge ports 12 are formed on a nozzle plate 15 at designated intervals, and the liquid chambers 13 are formed

on a base plate portion 16 parallel to the liquid discharge ports 12, respectively. Each of the liquid chambers 13 and the corresponding liquid discharge port 12 are connected respectively through the liquid flow path 16a formed on the base plate portion 16. Also, on the upper face of the base plate portion 16, the opening portion 16b is formed for each liquid chamber 13 correspondingly, and the oscillating plate 17 is formed to cover the opening portion 16b on the upper face of the base plate portion 16. Then, the piezoelectric film 14 is arranged on the oscillating plate 17 to be positioned corresponding to each liquid chamber 13.

[0054] Also, on the upper and lower faces of the piezoelectric film 14, electrodes 18 of Pt, Au, Al, or the like are positioned, as shown in Fig. 2C, and arranged on the oscillating plate 17, respectively. As the composition of the piezoelectric film 14, there may be usable such composition as lead zirconia titanate (PZT), barium titanate, or barium zirconia titanate having the perovskite structure, which is an oxide composed of lead, titanium, and zirconium or a composition obtainable by adding Mn, Nb, La, Ge, or some other element to any one of them. In this way, the piezoelectric film type actuator (piezoelectric oscillating portion) 19 is formed by the piezoelectric film 14 having the electrodes 18 formed therefor, and the oscillating plate 17, as well.

[0055] The liquid discharge head 11 is a device manufactured by the same method as the one for manufacturing the aforesaid piezoelectric film type actuator.

Particularly, each of the piezoelectric films is formed in parallel at high density, while each of the liquid chambers, which is formed on the base plate portion of the oscillating plate structural member formed by the oscillating plate and the base plate portion, is arranged in parallel at high density, the same as piezoelectric films. In this respect, for manufacturing the actuator, the base plate portion may be either a base plate having the liquid chamber processed in advance or a base plate with the liquid chamber yet to be processed. Also, the base plate portion may be integrally formed with the oscillating plate or bonded to the oscillating plate. The liquid chamber formed for the base plate is machined or etched to be the space where liquid flows in, and the liquid chamber may be configured to be rectangular, oval, or the like. Also, the liquid chamber is communicated with the liquid flow path into which liquid is supplied from a liquid tank. Also, between the liquid chamber and the liquid tank, means for preventing reverse flow may be processed.

[0056] Also, a plurality of piezoelectric films and liquid chambers of the oscillating plate structural member are formed respectively to correspond to each other to make it possible to form a liquid discharge head with good dimensional precision where the variation of dimensional precision of the piezoelectric film is

suppressed to be within $\pm 5\%$. Here, the dimensional precision of the piezoelectric film means that variations of the width, length, and height of the piezoelectric film are kept within $\pm 5\%$, respectively.

[0057] In order to enhance the bonding strength of the oscillating plate structural member and the piezoelectric film and the durability as the actuator and the liquid discharge head, it is preferable to make the surface roughness Ra of the piezoelectric film 0.01 μm to 2.5 μm . Then, with the surface roughness Ra of the piezoelectric film being kept within the aforesaid range, it becomes possible to obtain a device having a small variation of displacement between each element and that of oscillation characteristics. Here, a small variation of displacement means that the maximum amount of variation of the oscillating plate is kept within $\pm 7\%$. Also, a small variation of oscillating characteristics means that the increased or decreased amount of displacement is constant between each of the elements at frequencies 10 kHz to 25 kHz.

[0058] Next, a detailed description will be made of the method of the present invention for manufacturing a liquid discharge head in accordance with specific embodiments.

[0059] Figs. 3A, 3B and 3C to Fig. 7 are views, which schematically illustrate each specific process of the method for manufacturing a liquid discharge head in accordance with a first embodiment of the present invention.

[0060] In the step of forming a piezoelectric film on an intermediate transfer member, a polycrystal base plate of MgO in a size of 1 mm thick \times 5 cm long \times 1 cm wide is used as the intermediate transfer member 22. On the MgO intermediate transfer member 22, a rectangular mold 25 is formed at an interval of 300 dpi density using photosensitive resin 24, as shown in Figs. 3A and 3B.

[0061] Between each of the molds 25 formed on the MgO intermediate transfer member 22, a complex material layer 23 that contains carbon and SiO_2 is formed at first as shown in Fig. 3C. Then, on this layer, PZT (lead zirconia titanate) paste 21 is buried by means of screen printing. After that, a drying process is executed at a 100°C to 150°C . This process is repeated three time until the mold 25 is filled up to the height thereof (8 μm). Subsequently, the regular firing is made at a temperature of $1,200^\circ\text{C}$. With this regular firing, the resin 24 is fired at the same time. In this way, the PZT array is formed, as shown in Fig. 4, to arrange the rectangular PZT piezoelectric films 21 in parallel at a density of 300 dpi. The surface roughness Ra of this PZT array is 0.6 μm . At this juncture, the complex material layer 23 that contains carbon and SiO_2 , which is formed between the MgO intermediate transfer member 22 and the PZT piezoelectric film 21, is carbonized

when the piezoelectric film 21 is fired, and becomes the porous layer 23 (approximately 3 μm thick) the density of which is 85%.

[0062] In the next step, where the intermediate transfer member on the piezoelectric film and the oscillating plate structural member 26 are bonded, the oscillating plate structural member 25 to be bonded to the piezoelectric film 21 is structured, as shown in Fig. 5, by the oscillating plate 27 of SUS of 0.2 μm having the surface roughness Ra1 and the Si base plate portion 28 formed with the liquid chamber 29. When the oscillating plate structural member 26 and the PZT array formed as shown in Fig. 4 are bonded, the Pd layer 31 is filmed on the surface of the piezoelectric film 21 of the PZT array, as shown in Fig. 6, while the Pd layer 31 and the In layer 32 are filmed on the surface of the SUS oscillating plate 27 one after another. After contact is made, heating is conducted at a temperature of 250°C to form the PdIn₃ alloy layer 33 (see Fig. 7), hence bonding the piezoelectric film 21 and the oscillating plate 27 together.

[0063] Then, in the step of peeling off the intermediate transfer member from the piezoelectric film, the MgO intermediate transfer member 22 is peeled off from the piezoelectric film 21. In accordance with the present embodiment, the porous layer 23 is formed between the MgO intermediate transfer member 22 and the PZT piezoelectric film 21. It is therefore possible to peel them off mechanically with ease.

[0064] For the present embodiment, it is made possible to form an array of 300 PZT piezoelectric films 21 per 25.4 mm (per inch) and transfer and bond it to the oscillating plate structural member 26 without a dimensional variation. The dimensional variation of the actuator thus manufactured is within $\pm 3\%$.

[0065] Lastly, a silicon nozzle plate 34, which is formed with nozzles (liquid discharge ports) 35 arranged corresponding to liquid chambers 29, is bonded to the oscillating plate structural member 26 as shown in Fig. 7. Thus, an elongated and high density liquid discharge head (see Figs. 2A to 2C) is manufactured. Here, in Fig. 7, a reference numeral 36 designates upper electrodes.

[0066] Also, as the bonded alloy layer 33, it is possible to film Pd and In as a single layer, respectively, and bond it to one side or to provide the laminated layer of In/Pd for both sides and bond it thereto.

[0067] With the liquid discharge head thus manufactured, it becomes possible to perform discharges at a speed of 11 m/s at a driving voltage of 20 V and a frequency of 15 kHz.

[0068] Next, with reference to Figs. 8A to 8F, the description will be made specifically of the method for manufacturing a liquid discharge head in accordance with a second embodiment of the present invention.

[0069] In the step of forming the piezoelectric film on the intermediate transfer member in accordance with the present embodiment, the dispersing solution, in which the same amounts of Al_2O_3 particles of approximately $0.4\text{ }\mu\text{m}$ each and ZrO_2 particles of approximately $0.3\text{ }\mu\text{m}$ each are mixed, is added to a Si alkoxide solution and coated on the single crystal MgO intermediate member (65% average transmissivity of 230 to 260 nm) 52, as shown in Fig. 8A. Then, a heating treatment is performed at the maximum temperature of 430°C to burn and remove the organic component, hence forming a porous layer 53 of $9\text{ }\mu\text{m}$ thick having a density of 92%.

[0070] On the porous layer 53, PMN-PZT film 51 is formed in a thickness of $12\text{ }\mu\text{m}$ by the sintering process at a temperature of $1,100^\circ\text{C}$. The surface roughness R_a of the piezoelectric film 51 is $0.7\text{ }\mu\text{m}$. On this film, Pd layer 61 of 150 nm is filmed by means of sputtering. Further, In layer 62 of 900 nm is filmed thereon.

[0071] Also, as shown in Fig. 8B, there is prepared the oscillating plate structural member 56 in which the ZrO_2 oscillating plate (Young's modulus: 192 GPa) 57 of $5\text{ }\mu\text{m}$ thick is laminated on the SUS base plate 58 of $200\text{ }\mu\text{m}$ thick. The surface roughness R_{a1} of the oscillating plate 57 is $0.5\text{ }\mu\text{m}$. On the oscillating plate 57, Pd layer 61 of 120 nm is filmed.

[0072] Subsequently, as shown in Fig. 8C, the PZT piezoelectric film 51 and the oscillating plate structural member 56 are superposed, and a heating treatment is performed at 200°C for 30 minutes under a pressure of $2 \times 10^3\text{ kPa}$, thus forming an alloy layer 63 of PdIn_3 and bonding them.

[0073] After that, as shown in Fig. 8D, a water jet 65 of $15 \times 10^4\text{ kPa}$ is discharged by the water jet method onto the porous layer 53 to collapse the porous layer 53. In this way, the MgO intermediate transfer member 52 can be easily peeled off (see Fig. 8E).

[0074] Then, as shown in Fig. 8F, the piezoelectric film 51 bonded to the oscillating plate structural member 56 is patterned by an etching process with a resolution of 180 dpi. After that, the SUS base plate 58 is also etched to produce each of the liquid chambers 59 on the lower part of the piezoelectric film 51. Then, the silicon nozzle plate 66, which is provided with liquid discharge ports (nozzles) 67 arranged corresponding to the liquid chambers 59, respectively, is bonded to the oscillating plate structural member 56 for the formation of an elongated and high density liquid discharge head device. In this way, it is possible

to obtain the liquid discharge head (see Figs. 2A to 2C), which is provided with the piezoelectric film type actuator. The bonding strength of the ZrO_2 oscillating plate 57 and the piezoelectric film 51 is firm, and there is almost no reduction in the amount of displacement even after the durability test, which is executed 10^7 times at a driving voltage of 20 V at a frequency of 15 kHz.

[0075] Also, the piezoelectric film 51 is patterned to be in the form of array and then bonded to the oscillating plate structural member 56, and the intermediate transfer member 52 is peeled off by means of the water jet method. In this case, too, it is equally possible to obtain an excellent piezoelectric film type actuator. Also, when the bonding is made by a heating process at 450°C using SiO_2 for the bonding layer, a firm strength is obtainable therefor. Bonding at 500°C using Si_3N_4 also presents a firm strength.

[0076] Next, a method for manufacturing a liquid discharge head specifically in accordance with a third embodiment of the present invention will be described.

[0077] For the present embodiment, the piezoelectric film, which is formed in an array on the MgO intermediate transfer member (65% average transmissivity of 230 to 260 nm), is used. As in the case of the second embodiment described above, the piezoelectric film formed in the array is bonded to the oscillating plate structural member. After that, a laser beam is used as a means for peeling off the MgO intermediate transfer member.

[0078] Onto the portion where the piezoelectric film adheres, an excimer laser beam is irradiated from the MgO intermediate transfer member side at an energy of approximately 300 mJ/cm^2 . All the piezoelectric film portions are irradiated. After being left intact at room temperature, the MgO intermediate transfer member is peeled off. Then, the piezoelectric film can be separated therefrom with ease. Also, it is confirmed that peeling is equally possible by the irradiation of a YAG laser beam at an energy of 400 mJ/cm^2 .

[0079] Then, after a polymer protection film is provided for the piezoelectric film formed in array, the liquid chambers are produced by etching the SUS base plate. Subsequently, the protection film of the piezoelectric film is removed, and the piezoelectric film is rinsed by means of ion milling. Then, through the steps of the heating process and the Pt upper electrode formation process, a piezoelectric actuator is obtained.

[0080] With the piezoelectric type actuator thus manufactured, it is also confirmed that there is a sufficient amount of displacement up to a frequency of 30 kHz at a driving voltage of 20 V. Also, good corresponding displacements are confirmed with respect to the frequencies of the driving voltage. With this actuator, a liquid

discharge head is manufactured as in the embodiment described earlier, and the discharge condition is examined with the result that liquid droplets are discharged stably at a speed of 13 m/s at a driving voltage of 20 V at a frequency of 15 kHz.

[0081] Next, the method for manufacturing a liquid discharge head specifically in accordance with a fourth embodiment of the present invention will be described.

[0082] As a piezoelectric film for the present embodiment, the piezoelectric film, which is manufactured in the same way as the second embodiment described earlier, is used, and as the oscillating plate structural member thereof, the oscillating plate structural member, which is manufactured in the same way as the first embodiment described above, is used. These are bonded by the energized contact under pressure. A Ni layer is provided for the piezoelectric film. Then, after the provision of an Ag layer on the oscillating plate side, electricity of 20 A is applied from the oscillating plate side to the end of the piezoelectric film under a pressure of 2.0×10^3 kPa. After the bonding process, a water jet is discharged at the porous layer as in the second embodiment to effectuate peeling. The piezoelectric film type actuator thus manufactured presents sufficient displacements at a driving voltage of 30 V.

ABSTRACT OF THE DISCLOSURE

[0083] A method for manufacturing a piezoelectric film type actuator, which is provided with a piezoelectric film and an oscillating plate structural member bonded therefor, comprises the steps of forming a piezoelectric film on an intermediate transfer member; bonding the piezoelectric film on the intermediate member and the oscillating plate structural member; and peeling off the intermediate transfer member from the piezoelectric film. Through the steps thus arranged, it becomes possible to enhance the bonding strength and durability of the piezoelectric film and the oscillating plate structural member without using a bonding agent in the manufacture of a highly reliable piezoelectric film type actuator.

Substitute Specification
Application No. 09/977,972
Attorney Docket No. 03500.015881 - 1 -

CFO 15881-US

PIEZOELECTRIC FILM TYPE ACTUATOR,
LIQUID DISCHARGE HEAD,
AND METHOD OF MANUFACTURING THE SAME

5 BACKGROUND OF THE INVENTION

Field of the Invention

The present invention relates to a piezoelectric film type actuator used for a liquid discharge head, a sound generating device, such as ^amicrophone, a speaker,
10 various kinds of vibrators or oscillators, as well as a sensor or the like, and also, relates to the method of manufacturing the same. Further, the invention relates to a liquid discharge head that uses the piezoelectric film type actuator, and the method of manufacture
15 therefor. In this respect, the piezoelectric film type actuator referred to in the ^{subject} specification ~~hereof~~ ^{means is a} the member that converts electric energy to mechanical energy such as to effectuate mechanical displacements, vibrations, or stresses, ^{it is a} and ~~also, means the member~~
20 that ^{as reverse of} ~~makes~~ such conversion reversely.

Related Background Art

In recent years, ^{there} ~~it~~ has been ^a ~~in~~ demand ^{for} ~~to provide~~ a displacement element for adjusting the length and the position of optical path on ^a the order of sub-micron or
25 a sensing element for detecting micro displacements as electrical changes in the fields of optics and precision processing. To meet ^{this} ~~such~~ demand, there has

been in progress ^athe development of a piezoelectric film type actuator, which is a member that utilizes the displacement or the inverse phenomenon thereof based on the reverse piezoelectric effect or electric distortion when ^{an}electric field is applied to the piezoelectric or electrically distortional material of a ferroelectric element.

Also, conventionally, it has been preferred to adopt the unimorph type or the bimorph type for the formation of a piezoelectric film type actuator used for the liquid discharge recording head or the like. In this respect, for the liquid discharge recording apparatus that uses a piezoelectric film type actuator of the kind for the enhancement of the printing quality and the printing speed, among some others, in order to meet such demand, the development has been in progress for the implementation to make the piezoelectric film type actuator smaller ^{at a}in higher density, which can be driven at ^alower voltage, but with a higher ^{response}performance ~~of response~~, as well as for the provision of an elongated multiple nozzle.

Now, in order to obtain a large flexure displacement, a generating power, or a generation potential with the aforesaid unimorph- or bimorph- piezoelectric film type actuator, it is important to make the base plate that becomes the oscillating plate thinner. Here, however, the thickness of such ^abase

decreased and
plate is ~~made smaller~~ ² the strength thereof is reduced,
leading to the problem that the smoothness is lowered
eventually. ^{reduced} Further, there is a problem for the
conventional unimorph- or bimorph-piezoelectric film
5 type actuator that the reliability thereof is marred
due to ^{the} use of ^a bonding agent.

To overcome these problems, ^{it} ~~an art~~ is disclosed in
the specification of Japanese Patent Application Laid-
Open No. 62-213399 ^{an increased} to ~~provide a firmer~~ bonding strength ^{is provided}
10 by sintering piezoelectric ceramics and ceramics
oscillating plate at a time without using any bonding
agent.

However, in this method, different materials are
sintered at high temperature. As a result, the
15 oscillating plate and the piezoelectric ceramics are
shrunk themselves, ^{making} ~~to make~~ it difficult to adjust the
dimensional precision in the order of ^a micron on a large
area. For that matter, the highly reliable
piezoelectric film type actuator having a large area,
20 or the liquid discharge head, can hardly be obtained.

SUMMARY OF THE INVENTION

It is an object ^{of} of the present invention to
provide a highly reliable piezoelectric film type
25 actuator that can be ~~arranged in~~ ^{of} high integration,
^{ms} which makes it possible to obtain large displacements
at a low driving voltage with ^a high ^{response} speed of ~~responses~~.

and also, to provide a liquid discharge head that uses such piezoelectric film type actuator, as well as to provide the method of manufacture for each of ^{the above} ~~them~~.

It is another object of the invention to obtain a
5 method for manufacturing a piezoelectric film type
actuator having a piezoelectric film and an oscillating
plate structural member bonded therefor, which ^{to} ~~method~~
comprises the steps of forming a piezoelectric film on
an intermediate transfer member; bonding the
10 piezoelectric film on the intermediate member and the
oscillating plate structural member; and peeling off
the intermediate transfer member from the piezoelectric
film.

For the method of the present invention for
15 manufacturing a piezoelectric film type actuator, it is
preferable for the piezoelectric film to contain lead,
titanium, and zirconium. Also, the piezoelectric film
may be the one which is patterned.

For the method of the present invention for
20 manufacturing a piezoelectric, it is preferable that in
the step of bonding the piezoelectric film and the
oscillating plate structural member, the piezoelectric
film and the oscillating plate structural member are
bonded by means of energized heating, low temperature
25 heating, or energized contact under pressure through
a single metal, ^{an} alloy, ^a metal oxide, ^a metal nitride, or a
metallic compound. Also, it is preferable to make the

surface roughness Ra of the piezoelectric film 0.01 μm to 2.5 μm . More preferably, it is made 0.02 μm to 1.0 μm .

For the method of the present invention for
5 manufacturing a piezoelectric film type actuator, it is preferable that in the step of peeling off the intermediate transfer member from the piezoelectric film, the intermediate transfer member is peeled off by the irradiation of ^{Ar}_A laser beam, such as ^{Ar}_A excimer laser
10 beam or ^{Ar}_A infrared laser beam, among some others, through the intermediate transfer member.

For the method of the present invention for manufacturing a piezoelectric film type actuator, it is preferable that in the step of peeling off an
15 intermediate transfer member from a piezoelectric film, a fluid flux (water jet) is discharged between the intermediate transfer member and the piezoelectric film to peel off the intermediate transfer member. It is also preferable to form a porous layer having a
20 concentration of 30% to 95% between the intermediate transfer member and the piezoelectric film.

It is still another object of the present invention to provide a method for manufacturing a liquid discharge head provided with a base plate
25 portion having liquid discharge ports, liquid chambers connected with the liquid discharge ports, and a piezoelectric film type actuator formed by a

piezoelectric film and an oscillating plate provided
for a part of the liquid chambers, for discharging
liquid from the liquid discharge ports by means of the
flexural oscillation of the piezoelectric film type
5 actuator, which comprises the steps of forming a
piezoelectric film on an intermediate transfer member;
bonding the piezoelectric film on the intermediate
member and the oscillating plate structural member; and
peeling off the intermediate transfer member from the
10 piezoelectric film.

The piezoelectric film type actuator of the
present invention is characterized in that it is
manufactured by the aforesaid method for manufacturing
a piezoelectric film type actuator. Also, the liquid
15 discharge head of the present invention is
characterized in that it is manufactured by the
aforesaid method for manufacturing a liquid discharge
head.

In accordance with the present invention, the
20 piezoelectric film is not ~~filmed~~^{formed} directly on the
oscillating plate structural member, but through the
intermediate transfer member. The step of forming the
piezoelectric film and that of bonding the
piezoelectric film to the oscillating plate structural
25 member are separated. The film formation process of
the piezoelectric film and the manufacturing process of
the actuator ^{are} functionally separated. A wide

selection of material is made possible for the oscillating plate structural member as an actuator, hence obtaining an advantage to provide a film after adjusting the performance thereof arbitrarily as a piezoelectric film. Also, when the piezoelectric film and the oscillating plate structural member are bonded, it is possible to set the heating temperature at 500°C or less for bonding, and the surface roughness Ra of the piezoelectric film is defined to be 0.01 μm to 2.5 μm . Then, bonding is effectuated by means of energized heating, low heating, or energized contact under pressure through ^hmetal, ^{uw}alloy, ^ametal oxide, ^vmetal nitride, or ^ametallic compound. The bonding strength and durability are thus enhanced without using ^abonding agent ^{to} ~~for the~~ ^{de} ~~provision of~~ a highly reliable piezoelectric film type actuator.

Further, the intermediate transfer member can be peeled off easily mechanically or by the irradiation of ^a laser beam without damaging the piezoelectric film. As a result, the intermediate transfer member can be utilized again.

In this way, it becomes possible to obtain a piezoelectric film type actuator capable of providing a large area and high integration, as well as generating large power, with which a large displacement is obtainable at ^alow driving voltage with ^ahigh response speed. Further, it becomes possible to manufacture a

highly reliable elongated liquid discharge head in high density, which is capable of obtaining a large displacement at ^Nlow driving voltage with ^Ostable and high response.

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BRIEF DESCRIPTION OF THE DRAWINGS

Figs. 1A, 1B, 1C and 1D are views ^{that} ~~which~~ illustrate the main process of a method for manufacturing a piezoelectric film type actuator in accordance with the present invention.

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Fig. 2A is a perspective view, which shows a liquid discharge head in accordance with the present invention. Fig. 2B is a cross-sectional view, which shows the liquid discharge head represented in Fig. 2A, taken along line 2B - 2B in Fig. 2A. Fig. 2C is an enlarged cross-sectional view, which shows the piezoelectric film type actuator of the liquid discharge head of the present invention.

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Figs. 3A, 3B and 3C are views, which show the process of forming a piezoelectric film on an intermediate transfer member in accordance with the method for manufacturing a liquid discharge head embodying the present invention; Fig. 3A is a plan view showing the state of forming a resin pattern on an intermediate transfer member; Fig. 3B is a cross-sectional view taken along line 3B - 3B in Fig. 3A; and Fig. 3C is a cross-sectional view, which shows the state

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of burying a complex material layer and a piezoelectric film paste between a mold formed on the intermediate transfer member.

5 Fig. 4 is a perspective view, which shows the state of forming the piezoelectric film in an array by the process of forming the piezoelectric film on the intermediate transfer member in accordance with the method for manufacturing a liquid discharge head embodying the present invention.

10 Fig. 5 is a perspective view, which shows the structural member of an oscillating plate to be bonded to the piezoelectric film in the method for manufacturing a liquid discharge head embodying the present invention.

15 Fig. 6 is a cross-sectional view, which shows the process of bonding the piezoelectric film and the structural member of the oscillating plate in the method for manufacturing a liquid discharge head embodying the present invention.

20 Fig. 7 is a cross-sectional view, which shows the liquid discharge head manufactured by the method for manufacturing a liquid discharge head embodying the present invention.

25 Figs. 8A, 8B, 8C, 8D, 8E and 8F are views, which schematically illustrate the main process of the method for manufacturing a liquid discharge head in accordance with another embodiment of the present invention.

DETAILED DESCRIPTION OF THE PREFERRED EMBODIMENTS

Hereinafter, with reference to the accompanying drawings, ~~the description will be made of the~~ embodiments in accordance with the present invention ^{will be described}

5 Figs. 1A to 1D are the views, which illustrate the main process of a method for manufacturing a piezoelectric film type actuator in accordance with the present invention.

10 The main process of the method of manufacture for the piezoelectric film type actuator (hereinafter referred to simply as an actuator) in accordance with the present invention consists of the process of forming a piezoelectric film on an intermediate transfer member, the process of bending the
15 piezoelectric film on the intermediate transfer member to the structural member of an oscillating plate, and the process of peeling off the intermediate transfer member from the piezoelectric film as shown in Figs. 1A to 1D.

20 In the first process, that is, the process of forming the piezoelectric film on the intermediate transfer member, a porous layer 3 is formed on an intermediate transfer member 2 as shown in Fig. 1A. Then, piezoelectric film 1 is formed thereon.

25 For the formation of the piezoelectric film 1, it is possible to appropriately adopt the known method, such as sintering, sputtering, sol-gel, CVD,

hydrothermal synthesis, laser ablation, or gas deposition, among some others, and select the piezoelectric film composition and the method of manufacture, which can provide characteristics fit for an intended use. As the composition of the piezoelectric film 1, there may be usable such composition as lead zirconia titanate (PZT), barium titanate, or barium zirconia titanate having the perovskite structure, which is an oxide composed of lead, titanium, and zirconium or a composition obtainable by adding Mn, Nb, La, Ge, or some other element to any one of them. As the crystallinity of the piezoelectric film, either ^apolycrystalline element or ^asingle crystalline element may be usable. Also, as the mode of the piezoelectric film 1, a patterned mode is represented in Fig. 1A, but various modes may be ~~used~~ ^{employed} depending on usage, and the mode is not necessarily limited to the patterned one. As the patterning method, there is the one that dry or wet etches a solid film, performs sand blasting or cutting process mechanically, or patterns after forming a metal mask or resist at the time of film formation. Further, there is a lift-off method where a highly precise mold is formed with ~~resin~~ ^a of light hardening type, and ^aPZT paste is buried in-between. The film thickness of the piezoelectric film 1 is 0.1 μ m to 20 μ m, or preferably, 0.5 μ m to 12 μ m.

Also, as the intermediate transfer member 2 that forms the piezoelectric film 1, inorganic oxide, such as alumina, zirconia, magnesia, or sapphire, is used. Here, ^asingle crystal may be used depending on usage.

5 Also, the film thickness of the intermediate transfer member 2 it is preferable to set ~~it~~ at 10 μ m to 5 mm or more preferably, 100 μ m to 2 mm. If the film thickness of the intermediate transfer member 2 is ~~made~~ less than 10 μ m, a problem is encountered ⁱⁿ that it becomes unfavorable to maintain the shape of the piezoelectric film 1, and also, ^{in that} it becomes difficult to handle the piezoelectric film for bonding at the next step. Also, it is not preferable to make the film thickness more than 5 mm, because there is then a problem ⁱⁿ that the intermediate transfer member 2 cannot be peeled off easily without damaging the piezoelectric film 1 when peeled from the intermediate transfer member 2 after bonding. Also, on the intermediate transfer member 2, electrodes for actuator use can be formed in advance. Here, as described later, there may be the case where the optical property or the layer structure of the intermediate transfer member 2 is limited depending on the method of peeling in the peeling process subsequent to bonding.

25 The porous layer 3 is formed to make it easier to peel off the intermediate transfer member 2 after the piezoelectric film 1 is bonded to the oscillating plate

structural member 4. It is preferable to form the porous layer 3 with ^a material containing carbon or non-sintering ceramics. For example, then, on the intermediate transfer member 2, a layer that contains carbon and metallic oxide is formed in advance, and the piezoelectric film 1 and the intermediate transfer member 2 are separated by breaking the brittle porous layer 3 when the layer that contains carbon becomes a brittle metal oxide layer due to heat from firing the piezoelectric film 1. In this way, the intermediate transfer member 2 can be peeled off easily. Here, as described later, depending on the peeling method, such as using the irradiation of laser beam, for example, it is possible to peel off the intermediate transfer member 2 without any intervention of the porous layer 3.

Also, the surface roughness R_a on the side of the piezoelectric film 1 where it is bonded to the oscillating plate structural member 4 should desirably be within a range of 0.01 μm to 2.5 μm . More preferably, it is within a range of 0.02 μm to 1.0 μm . It is preferable to keep the surface roughness R_a of the piezoelectric film 1 within the surface roughness R_a of the aforesaid range in order to enhance the durability of the actuator, while making it possible to bond the piezoelectric film 1 to the oscillating plate structural member 4 at lower temperature under lower

pressure (see Fig. 1B). If the surface roughness R_a of the piezoelectric film 1 is less than $0.01 \mu\text{m}$, the bonding strength becomes insufficient, and a problem may be encountered in some casesⁱⁿ that the structure member 4 of the oscillating plate and the piezoelectric film 1 are peeled off in the peeling step in the following process. Also, it is not preferable to allow the surface roughness R_a of the piezoelectric film to exceed $2.5 \mu\text{m}$, because then the characteristics of the actuator (characteristics of its displacement and frequency) ~~are made~~^{become} defective. With the surface roughness R_a of the piezoelectric film 1 being kept within the range as described above, it becomes possible to obtain a good bonding strength, and a highly reliable actuator in particular. Also, the surface roughness R_{a1} of the oscillating plate 5 of the structural member 4 thereof, which is in contact with the piezoelectric film 1, should desirably be such as to make the difference of absolute values, $|R_{a1} - R_a|$, $0.5 \mu\text{m}$ or less with respect to the surface roughness R_a of the piezoelectric film 1. Here, the surface roughness can be measured by ~~use of~~^{using} a surface roughness meter "Surfcoder" manufactured by Kosaka Institute.

Now, in the second process, which is the step of bonding the piezoelectric film to the oscillating plate structural member, there is formed the oscillating plate structural member 4 with the oscillating plate 5

and the base plate portion 6 that constitute the actuator as shown in Fig. 1B. Here, the oscillating plate 5 and the base plate 6 may be formed integrally or bonded together. For the oscillating plate structural member 4, heat resistance is needed so that it is not deformed by heat when bonded to the piezoelectric film 1. It is preferable to use^a material having a heat resistance of 150°C or more. In this respect, the heat resistance of 150°C or more means that the possible dimensional displacement is less than 3% after a heat treatment ~~given~~^{ah} under atmosphere at 150°C for a period of 30 minutes.

For the oscillating plate 5, a material having the Young's modulus of 50 GPa or more, such as SUS, Ti, zirconia, Si, Cu, SiO₂, glass, or Cr, is usable. The oscillating plate 5 may be ^aone-layer structure or ~~of a~~ plural-layer structure. Even in a case of the plural-layer structure, there is a need for providing the Young's modulus of 50 GPa or more as a whole. The film thickness of the oscillating plate 5 is 0.5 μm to 20 μm. More preferably, it is 1 μm to 10 μm. Also, for the oscillating plate 5, it may be possible to use the one which is doped with a minute amount of ^ametal, such as Y or B.

The material of the base plate 6 of the oscillating plate structural member 4 may be ~~one and~~ the same^{as the} material of the oscillating plate 5, but a

ceramics compound material that contains alumina, cellcyan, magnesia, or carbon fiber may be useable as another material therefor. When the actuator is applied to a liquid discharge head, it may be possible to use ^aSi base plate or ^aSUS base plate for the base plate portion 6, for example, which is processed to have formed a liquid chamber in advance or yet to be processed to provide a liquid chamber in the post process that may follow. The liquid chamber of the liquid discharge head can be formed by machining, etching, or the like.

Then, when the piezoelectric film 1 and the oscillating plate structural member 4 are bonded, a bonding layer 7 (or bonding layers 7a and 7b) of ^ametal, ^ametal alloy, ^ametal oxide, ^ametal nitride, or ^ametallic compound substance is filmed on both ^{the} surface of the piezoelectric film 1 and ^{of the} oscillating plate 5 to be bonded or on either one ^{of these} surfaces ~~thereof~~ as shown in Fig. 1B. As the metal or alloy to be filmed on the surfaces of the oscillating plate structural member 14 and piezoelectric member 11 to form the bonding layers 7 (7a and 7b), ^ametal of at least one kind or more is usable among Pd, In, Sn, Ni, Ga, Cu, Ag, Mo, Ti, Zr or some other metal, and also, as the alloy, PdIn₃, Al-Cu, Ti-Ni, or the like is usable. As the metal oxide, there is SiO₂, CaO₂, TiO₂, ZnO, or the like, for example. As the metal nitride, there is TiN, Si₃N₄, or

the like, for example. As the metallic compound substance, there is Ti-Ni, Ag-Ni, Fe-Co, Cr-Mo, or the like, for example. In this manner, on both surfaces or either one of the surfaces of the oscillating plate structural member 4 and the piezoelectric member 1, the bonding layer 7 (7a and 7b) is filmed, and after these members abut against each other, both of them are bonded by energized heating, energized contact under pressure, low-temperature heating, or the like.

10 Here, the energized heating used for bonding is a method of bonding by means of heat generated ~~by itself~~ when current flows through a conductive layer. The quantity of current is 0.5 A/cm^2 to 200 A/cm^2 or preferably it is 1 A/cm^2 to 50 A/cm^2 . The energized contact under pressure is a method of ^{a still firmer} bonding ~~firmer~~ ~~still~~ by exerting pressure in addition to the aforesaid energized heating method. Also, the low-temperature heating is a method of bonding by forming ^{an} alloy on the bonding surfaces with a combination of different kinds of metals ^{that forms} alloy ^{at} a temperature of 300°C or less. Particularly, with a combination of Pd and In, it is possible to form ^{an} ~~the~~ alloy of PdIn_3 at about 250°C . Therefore, this combination is preferable for a bonding at ^a lower temperature. Besides this combination, it is possible to ~~perform~~ bonding by the combinations ^{ing} of Ag-Ni, Ti-Ni, Zr-Cu, among some others.

The third process, which is a step of peeling off

the piezoelectric film from the intermediate transfer member, is that, as shown in Fig. 1C, the intermediate transfer member 2 is cut off from the actuator, which is formed by bonding the piezoelectric film 1 and the oscillating plate structural member 4. As the technique used for peeling off the intermediate transfer member 2, there is ~~the one whereby to provide~~ a porous layer 3 ^{is provided} between the intermediate transfer member 2 and the piezoelectric film 1, and ~~destroy~~ this porous layer 3 ^{is} mechanically ^{is destroyed} so as to peel off the intermediate transfer member 2. There is also the one whereby ~~to destroy~~ the intermediate transfer member 2 ^{is destroyed} by a water jet method so as to peel ~~off it~~ or to peel off the intermediate transfer member 2 by means of rapid heating by the irradiation of ^a laser beam. In this respect, no porous layer 3 may be required for the technique that employs the irradiation of ^a laser beam for peeling.

For the application of the former two techniques (mechanical peeling and peeling by the water jet method), it is preferable to form a porous layer 3 of 30% to 95% concentration or preferably that of 50% to 95% concentration on the interface between the piezoelectric film 1 and the intermediate transfer member 2 when the piezoelectric film 1 is formed. The film thickness of the porous layer 3 is 0.5 μ m to 200 μ m or preferably 1.0 μ m to 100 μ m. ^{with} ~~As regards~~ ^{to} this

porous layer 3, the ceramic oxide layer that contains carbon is produced in advance on the intermediate transfer member 2, for example, and a porous layer is formed on the interface by carbon, which is fired when
5 the piezoelectric film 1 is fired at a high temperature, and then, this brittle porous layer is mechanically destroyed to easily peel off the piezoelectric film 1 from the intermediate transfer member 2. In this respect, the concentration of the
10 porous layer can be determined with the measurement of the aperture area by observing the section of the porous layer using a TEM (Transparent Electronics Microscope).

Further, it is a preferable mode that conductivity
15 is ^{provided} ~~given~~ to the porous layer 3 ^{to} ~~for the~~ utilization ^e thereof as the actuator electrodes. In such a case, a paste, which is prepared by the dispersion and mixture of metallic particles, carbon material, and ceramic particles in a solgel solution of SRO (strontium
20 ruthenium oxide) or ITO, is coated to produce a film, thus obtaining a conductive porous layer.

Also, when the intermediate transfer member 2 is peeled off through the porous layer 3, it becomes easier to separate them with the collision of a highly
25 pressurized fluid flux (water jet) with the porous layer 3. Generally, the water jet method is such as to cut or process ceramics, metal, resin, rubber, or

woods, or perform a surface rinsing or the like by discharging a highly pressurized flux of water flow onto an object at high speed. As an example in which the water jet method is used, there are the following disclosures:

K. Ohmi et al. "Water Jet Splitting of Thin Porous Si for ELTRAN", The Japan Society of Applied Physics, Tokyo, pp. 345 to 355 (1999); and

R. Herino et al. "Microstructure of Porous Silicon and its Evaluation with Temperature", Mater. Lett. 2, pp. 519 to 523 (1984). In accordance with the present invention, the water jet is discharged to the porous layer 3 to selectively collapse the porous layer 3 so as to enable the intermediate transfer member 2 to be separated. The pressure of the fluid used as the water jet is 5.0×10^4 kPa to 80.0×10^4 kPa or preferably, 10.0×10^4 to 50.0×10^4 kPa.

With *to* *of* *ins*
As regards the technique ~~to~~ peel off the intermediate transfer member by ~~the~~ irradiation *of a* laser beam, the piezoelectric film 1 is formed on the intermediate transfer member 2, and then, after an oscillating plate structural member 4 is bonded thereto, *a* laser beam is irradiated *onto* ~~to~~ the piezoelectric film 1 from the opposite side of the oscillating plate 5 through the intermediate transfer member 2 for rapid heating, and by the difference in the instantaneous thermal expansion or thermal decomposition, the

piezoelectric film 1 and the intermediate transfer member 2, which is a transparent base plate, are separated. As ^{an} laser beam, ^{an} excimer laser or ^{an} infrared laser can be used. When ^{an} excimer laser beam is applied, a material having a transmittance of 20% or more for light of 230 nm to 260 nm wavelength is used as the intermediate transfer member 2. Also, when ^{an} infrared laser beam is applied, a material having a transmittance of 20% or more for 700 nm to 1,250 nm is used as the intermediate transfer member. As the irradiating energy of the laser beam, it is preferable to apply 50 to 1,000 mJ/cm².

When ^{an} excimer laser beam is used for peeling, the intermediate transfer member 2 is ^{sufficient} ~~good~~ enough if a material used therefor has a transmissivity of approximately 230 nm to 260 nm, while withstanding a temperature of 900°C or more at the time of firing the piezoelectric film array. Then, the intermediate transfer member functions sufficiently when this method is applied, and MgO substrate, alumina, sapphire, quartz glass, CaCO₃, LiF, or the like can be used, for example. Also, when peeling is effectuated by use of ^{an} infrared laser, such as ^a carbon gas laser, ^{or a} ^Y YAG laser, the material, which presents a translucency of approximately 700 nm to 1,250 nm, while withstanding a temperature of 900°C or more at the time of firing the piezoelectric film array, can function sufficiently as

the intermediate transfer member for this method, and MgO, MgF₂, Y₂O₃, CaF₂, quartz glass, alumina, sapphire, or SrTiO₃ single crystal substrate can be used, among some others.

5 In the processes described above, the piezoelectric film type actuator is formed with the piezoelectric film 1 and the oscillating plate structural member 4 being bonded as shown in Fig. 1D. Here, in Fig. 1D, a reference numeral 9 designates
10 upper electrodes.

 In the manufacture of the piezoelectric film type actuator as described above, the process to form the piezoelectric film 1 and the process to bond the piezoelectric film 1 to the oscillating plate
15 structural member 4 are separated, and the film formation process of the piezoelectric film 1 and the manufacturing process of the oscillating plate structural member are functionally separated.
Therefore, ^{there is a wide selection of that used} materials can be selected ~~widely from among~~
20 ~~various ones~~ ^{(that} for the oscillating plate structural member 4 serving as the actuator. Further, there is an advantage ⁱⁿ that the film is obtainable after arbitrarily adjusting the performance of the piezoelectric film 1.

 When the piezoelectric film and the oscillating
25 plate structural member are bonded, the heating temperature can be set at as low as 500°C or less for bonding. Also, with the surface roughness Ra of the

piezoelectric film being 0.01 μ m to 2.5 μ m, bonding is made by means of energized heating, low temperature heating, energized contact under pressure, or the like through [^]metal, ^{an}alloy, ^ametal oxide, ^ametal nitride, or ^ametallic compound without using any bonding agent. In this way, it becomes possible to enhance the bonding strength and durability, thus obtaining a highly reliably piezoelectric film type actuator. Further, the intermediate transfer member can be peeled off mechanically or by the irradiation of ^alaser through the porous layer easily without ~~giving any~~ ^{ing} damage ^{to} the piezoelectric film. Also, the intermediate transfer member can be utilized again.

In this way, it becomes possible to obtain an element capable of obtaining a large displacement at a lower driving voltage with a large generating power at a faster response, which ~~can~~ ^{also} provide a large area for a higher integration arrangement. Thus, a highly reliable, large-area piezoelectric film type actuator can be manufactured, which can be preferably utilized for a sound generating device, such as ^amicrophone, ^aspeaker, various kinds of vibrator~~s~~ and oscillator~~s~~ and various kinds of sensors, such as an acceleration sensor, a pressure sensor, a vibration sensor, an angular velocity sensor, in addition to a liquid discharge head.

Next, with reference to Figs. 2A, 2B and 2C to

Figs. 8A, 8B, 8C, 8D, 8E and 8F, ~~the description will be made of~~ a liquid discharge head to be manufactured using the method for manufacturing the piezoelectric film type actuator of the present invention, and the
5 method of manufacture thereof, ~~as well.~~ *of, will be described*

A liquid discharge head 11 of the present invention ~~is structured as follows~~ *has* with a plurality of liquid discharge ports 12; the liquid chamber 13, which is installed for each of the liquid discharge ports 12;
10 and each the piezoelectric films 14 arranged for each of the liquid chambers 13, respectively, as shown in Fig. 2A and Fig. 2B. Here, in Figs. 2A and 2B, the liquid discharge ports 12 are arranged on the lower end side, but these ports can be on the side end side.

15 For the liquid discharge head 11, the liquid discharge ports 12 are formed on a nozzle plate 15 at designated intervals, and the liquid chambers 13 are formed on a base plate portion 16 ~~in~~ parallel
~~corresponding~~ to the liquid discharge ports 12,
20 respectively. Each of the liquid chambers 13 and the corresponding liquid discharge port 12 are connected respectively through the liquid flow path 16a formed on the base plate portion 16. Also, on the upper face of the base plate portion 16, the opening portion 16b is
25 formed for each liquid chamber 13 correspondingly, and the oscillating plate 17 is formed to cover the opening portion 16b on the upper face of the base plate portion

16. Then, the piezoelectric film 14 is arranged on the oscillating plate 17 to be positioned corresponding to each liquid chamber 13.

Also, on the upper and lower faces of the
5 piezoelectric film 14, electrodes 18 of Pt, Au, Al, or the like are positioned, as shown in Fig. 2C, and arranged on the oscillating plate 17, respectively. As the composition of the piezoelectric film 14, there may be usable such composition as lead zirconia titanate
10 (PZT), barium titanate, or barium zirconia titanate having the perovskite structure, which is an oxide composed of lead, titanium, and zirconium or a composition obtainable by adding Mn, Nb, La, Ge, or some other element to any one of them. In this way,
15 the piezoelectric film type actuator (piezoelectric oscillating portion) 19 is formed by the piezoelectric film 14 having the electrodes 18 formed therefor, and the oscillating plate 17, as well.

The liquid discharge head 11 is a device
20 manufactured by the same method as the one for manufacturing the aforesaid piezoelectric film type actuator. Particularly, each of the piezoelectric films is formed in parallel ^{at} ~~in~~ high density, while each of the liquid chambers, which is formed on the base
25 plate portion of the oscillating plate structural member formed by the oscillating plate and the base plate portion, is arranged in parallel ^{at} ~~in~~ high density,

the same as piezoelectric films. In this respect, for manufacturing the actuator, the base plate portion may be either a base plate having the liquid chamber processed in advance or a base plate ~~for which~~ ^{with the} liquid chamber ~~yet~~ ^{to} be processed. Also, the base plate portion may be integrally formed with the oscillating plate or bonded to the oscillating plate. The liquid chamber formed for the base plate is machined or etched to be the space where liquid flows in, and the liquid chamber may be configured to be rectangular, oval, or the like. Also, the liquid chamber is communicated with the liquid flow path into which liquid is supplied from a liquid tank. Also, between the liquid chamber and the liquid tank, means for preventing reverse flow may be processed.

Also, a plurality of piezoelectric films and liquid chambers of the oscillating plate structural member are formed respectively to correspond to each other to make it possible to form a liquid discharge head with good dimensional precision where the variation of dimensional precision of the piezoelectric film is suppressed to be within $\pm 5\%$. Here, the dimensional precision of the piezoelectric film means that variations of the width, length, and height of the piezoelectric film are kept within $\pm 5\%$, respectively.

In order to enhance the bonding strength of the oscillating plate structural member and the

piezoelectric film and the durability as the actuator and the liquid discharge head, it is preferable to make the surface roughness Ra of the piezoelectric film 0.01 μm to 2.5 μm . Then, with the surface roughness Ra of the piezoelectric film being kept within the aforesaid range, it becomes possible to obtain a device ~~having~~ *having a* small ~~amount of~~ *variation of* displacement between each elements *and* that of oscillation characteristics. Here, a small ~~amount of~~ *variation of* displacement means that the maximum amount of variation of the oscillating plate is kept within $\pm 7\%$. Also, a small ~~amount of~~ variation of oscillating characteristics means that the increased or decreased amount of displacement is constant between each of the elements at frequencies 10 kHz to 25 kHz.

Next, ~~the~~ *a* detailed description will be made of the method of the present invention for manufacturing a liquid discharge head in accordance with specific embodiments.

Figs. 3A, 3B and 3C to Fig. 7 are views, which schematically illustrate each specific process of the method for manufacturing a liquid discharge head in accordance with a first embodiment of the present invention.

In the step of forming a piezoelectric film on an intermediate transfer member, a polycrystal base plate of MgO in a size of 1 mm thick \times 5 cm long \times 1 cm wide

is used as the intermediate transfer member 22. On the MgO intermediate transfer member 22, a rectangular mold 25 is formed at an interval of 300 dpi density using photosensitive resin 24, as shown in Figs. 3A and 3B.

5 Between each of the molds 25 formed on the MgO intermediate transfer member 22, a complex material layer 23 that contains carbon and SiO_2 is formed at first as shown in Fig. 3C. Then, on this layer, PZT (lead zirconia titanate) paste 21 is buried by means of
10 screen printing. After that, ^adrying process is executed at a 100°C to 150°C . This process is repeated three time until the mold 25 is filled up to the height thereof ($8\text{ }\mu\text{m}$). Subsequently, the regular firing is made at a temperature of $1,200^\circ\text{C}$. With this regular
15 firing, the resin 24 is fired at the same time. In this way, the PZT array is formed, as shown in Fig. 4, to arrange the rectangular PZT piezoelectric films 21 in parallel at ^{a density}~~intervals~~ of 300 dpi ~~density~~. The surface roughness R_a of this PZT array is $0.6\text{ }\mu\text{m}$. At
20 this juncture, the complex material layer 23 that contains carbon and SiO_2 , which is formed between the MgO intermediate transfer member 22 and the PZT piezoelectric film 21, is carbonized when the piezoelectric film 21 is fired, and becomes the porous
25 layer 23 (approximately $3\text{ }\mu\text{m}$ thick) the density of which is 85%.

In the next step, where the intermediate transfer

member on the piezoelectric film and the oscillating plate structural member 26 are bonded, the oscillating plate structural member 25 to be bonded to the piezoelectric film 21 is structured, as shown in Fig. 5, by the oscillating plate 27 of SUS of 0.2 μm having the surface roughness R_{al} and the Si base plate portion 28 formed with the liquid chamber 29. When the oscillating plate structural member 26 and the PZT array formed as shown in Fig. 4 are bonded, the Pd layer 31 is filmed on the surface of the piezoelectric film 21 of the PZT array, as shown in Fig. 6, while the Pd layer 31 and the In layer 32 are filmed on the surface of the SUS oscillating plate 27 one after another. After ^{contact is} ~~these are made in contact~~, heating is ^{conducted} ~~given~~ at a temperature of 250°C to form the PdIn_3 alloy layer 33 (see Fig. 7), hence bonding the piezoelectric film 21 and the oscillating plate 27 together.

Then, in the step of peeling off the intermediate transfer member from the piezoelectric film, the MgO intermediate transfer member 22 is peeled off from the piezoelectric film 21. In accordance with the present embodiment, the porous layer 23 is formed between the MgO intermediate transfer member 22 and the PZT piezoelectric film 21. It is therefore possible to peel them off mechanically with ease.

For the present embodiment, it is made possible to form an array of 300 PZT piezoelectric films 21 per

25.4 mm (per inch) and transfer and bond it to the oscillating plate structural member 26 without Δ dimensional variation. The dimensional variation of the actuator thus manufactured is within $\pm 3\%$.

5 Lastly, a silicon nozzle plate 34, which is formed with nozzles (liquid discharge ports) 35 arranged corresponding to liquid chambers 29, is bonded to the oscillating plate structural member 26 as shown in Fig. 7. Thus, an elongated and high density liquid
10 discharge head (see Figs. 2A to 2C) is manufactured. Here, in Fig. 7, a reference numeral 36 designates upper electrodes.

 Also, as the bonded alloy layer 33, it is possible to film Pd and In as a single layer, respectively, and
15 bond it to one side or to provide the laminated layer of In/Pd for both sides and bond it thereto.

 With the liquid discharge head thus manufactured, it becomes possible to perform discharges at a speed of 11 m/s at a driving voltage of 20 V and a frequency of
20 15 kHz.

 Next, with reference to Figs. 8A to 8F, the description will be made specifically of the method for manufacturing a liquid discharge head in accordance with a second embodiment of the present invention.

25 In the step of forming the piezoelectric film on the intermediate transfer member in accordance with the present embodiment, the dispersing solution, in which

the same amounts of Al_2O_3 particles of approximately 0.4 μm each and ZrO_2 particles of approximately 0.3 μm each are mixed, is added to ~~sol~~ ^a solution of Si alkoxide and coated on the single crystal MgO intermediate member

5 (65% average transmissivity of 230 to 260 nm) 52, as shown in Fig. 8A. Then, a heating treatment is ~~given~~ ^{performed} ~~thereto~~ at the maximum temperature of 430°C to ~~fire~~ ^{burn} ~~remove the~~ organic component ~~for the removal thereof~~, hence forming a porous layer 53 of 9 μm thick having a

10 density of 92%.

On the porous layer 53, PMN-PZT film 51 is formed in a thickness of 12 μm by the sintering process at a temperature of 1,100°C. The surface roughness R_a of the piezoelectric film 51 is 0.7 μm . On this film, Pd

15 layer 61 of 150 nm is filmed by means of sputtering. Further, In layer 62 of 900 nm is filmed thereon.

Also, as shown in Fig. 8B, there is prepared the oscillating plate structural member 56 in which the ZrO_2 oscillating plate (Young's modulus: 192 GPa) 57 of 5 μm

20 thick is laminated on the SUS base plate 58 of 200 μm thick. The surface roughness R_{a1} of the oscillating plate 57 is 0.5 μm . On the oscillating plate 57, Pd layer 61 of 120 nm is filmed.

Subsequently, as shown in Fig. 8C, the PZT

25 piezoelectric film 51 and the oscillating plate structural member 56 are superposed, and a heating treatment is ~~given~~ ^{performed} at 200°C for 30 minutes under a

pressure of 2×10^3 kPa, thus forming an alloy layer 63 of PdIn₃ and bonding them.

After that, as shown in Fig. 8D, a water jet 65 of 15×10^4 kPa is discharged by the water jet method onto the porous layer 53 to collapse the porous layer 53. In this way, the MgO intermediate transfer member 52 can be easily peeled off (see Fig. 8E).

Then, as shown in Fig. 8F, the piezoelectric film 51 bonded to the oscillating plate structural member 56 is patterned by ^{an} ~~means of~~ etching process with a resolution of 180 dpi. After that, the SUS base plate 58 is also etched to produce each of the liquid chambers 59 on the lower part of the piezoelectric film 51. Then, the silicon nozzle plate 66, which is provided with liquid discharge ports (nozzles) 67 arranged corresponding to the liquid chambers 59, respectively, is bonded to the oscillating plate structural member 56 for the formation of an elongated and high density liquid discharge head device. In this way, it is possible to obtain the liquid discharge head (see Figs. 2A to 2C), which is provided with the piezoelectric film type actuator. The bonding strength of the ZrO₂ oscillating plate 57 and the piezoelectric film 51 is firm, and there is almost no reduction in the amount of displacement even after the durability test, which is executed 10^7 times at a driving voltage of 20 V at a frequency of 15 kHz.

Also, the piezoelectric film 51 is patterned to be in the form of array^g and then^g bonded to the oscillating plate structural member 56, and the intermediate transfer member 52 is peeled off by means of the water jet method. In this case, too, it is equally possible to obtain an excellent piezoelectric film type actuator. Also, when the bonding is made by a heating process at 450°C using SiO₂ for the bonding layer, a firm strength is obtainable therefor. Bonding at 500°C using Si₃N₄ also presents a firm strength.

~~Next, the description will be made of a method for manufacturing a liquid discharge head specifically in accordance with a third embodiment of the present invention.~~ ^{will be described}

For the present embodiment, the piezoelectric film, which is formed in^{an} array on the MgO intermediate transfer member (65% average transmissivity of 230 to 260 nm), is used^g and^{As} in the case of the second embodiment described above, the piezoelectric film formed in^{the} array is bonded to the oscillating plate structural member. After that, ^a laser beam is used as a means for peeling off the MgO intermediate transfer member.

^{onto} to the portion where the piezoelectric film adheres, ^{an} excimer laser beam is irradiated from the MgO intermediate transfer member side at an energy of approximately 300 mJ/cm². All the piezoelectric film

portions are irradiated, and after being left intact at room temperature, the MgO intermediate transfer member is peeled off. Then, the piezoelectric film can be separated therefrom with ease. Also, it is confirmed
5 that peeling is equally possible by the irradiation of a YAG laser beam at an energy of 400 mJ/cm².

Then, after a polymer protection film is provided for the piezoelectric film formed in array, the liquid chambers are produced by etching the SUS base plate.
10 Subsequently, the protection film of the piezoelectric film is removed, and the piezoelectric film is rinsed by means of ion milling. Then, through the steps of the heating process and the Pt upper electrode formation process, a piezoelectric actuator is obtained.

15 With the piezoelectric type actuator thus manufactured, ~~too~~ ^{also} it is confirmed that ^{there is} a sufficient amount of displacement up to a frequency of 30 kHz at a driving voltage of 20 V. Also, good corresponding displacements are confirmed with respect to the
20 frequencies of the driving voltage. With this actuator, a liquid discharge head is manufactured as in the embodiment described earlier, and the discharge condition is examined with the result that liquid droplets are discharged stably at a speed of 13 m/s at
25 a driving voltage of 20 V at a frequency of 15 kHz.

Next, ~~the description will be made of~~ the method for manufacturing a liquid discharge head specifically

in accordance with a fourth embodiment of the present invention *will be described*

As a piezoelectric film for the present embodiment, the piezoelectric film, which is
5 manufactured in the same way as the second embodiment described earlier, is used, and as the oscillating plate structural member thereof, the oscillating plate structural member, which is manufactured in the same way as the first embodiment described above, is used.
10 These are bonded by ~~means of~~ ^a the energized contact under pressure. [^] Ni layer is provided for the piezoelectric film. Then, after the provision of ^{an} Ag [^] layer on the oscillating plate side, electricity of 20 A is ~~energized~~ ^{applied} from the oscillating plate side to the
15 end of the piezoelectric film under a pressure of 2.0×10^3 kPa. After ^{the} bonding process, ^a water jet is discharged ^{at} ~~to~~ the porous layer as in the second embodiment to effectuate peeling. The piezoelectric film type actuator thus manufactured presents sufficient
20 displacements at a driving voltage of 30 V.

WHAT IS CLAIMED IS:

1. A method for manufacturing a piezoelectric film type actuator having a piezoelectric film and an oscillating plate structural member bonded therefor comprising the following steps of:
 - forming a piezoelectric film on an intermediate transfer member;
 - bonding the piezoelectric film on said intermediate member and said oscillating plate structural member; and
 - peeling off said intermediate transfer member from said piezoelectric film.
2. A method for manufacturing a piezoelectric film type actuator according to Claim 1, wherein said piezoelectric film contains lead, titanium, and zirconium.
3. A method for manufacturing a piezoelectric film type actuator according to Claim 1, wherein said piezoelectric film is patterned.
4. A method for manufacturing a piezoelectric film type actuator according to Claim 1, wherein the surface roughness Ra of said piezoelectric film is 0.01 μm to 2.5 μm .

5. A method for manufacturing a piezoelectric film type actuator according to Claim 1, wherein in the step of bonding the piezoelectric film and the oscillating plate structural member, said piezoelectric film and said oscillating plate structural member are bonded by means of energized heating, low temperature heating, or energized contact under pressure through single metal, alloy, metal oxide, metal nitride, or metallic compound.

10

6. A method for manufacturing a piezoelectric film type actuator according to Claim 1, wherein in the step of peeling off the intermediate transfer member from the piezoelectric film, said intermediate transfer member is peeled off by the irradiation of laser beam from the intermediate transfer member side.

15

7. A method for manufacturing a piezoelectric film type actuator according to Claim 6, wherein said laser beam is an excimer laser beam.

20

8. A method for manufacturing a piezoelectric film type actuator according to Claim 6, wherein said laser beam is an infrared laser beam.

25

9. A method for manufacturing a piezoelectric film type actuator according to Claim 7, wherein the

transmissivity of 230 to 260 nm wavelength of said intermediate transfer member is 20% or more.

10. A method for manufacturing a piezoelectric film type actuator according to Claim 8, wherein the transmissivity of 700 nm to 1,250 nm wavelength of said intermediate transfer member is 20% or more.

11. A method for manufacturing a piezoelectric film type actuator according to Claim 1, wherein in the step of peeling off an intermediate transfer member from a piezoelectric film, a fluid flux is discharged between the intermediate transfer member and the piezoelectric film to peel off said intermediate transfer member.

12. A method for manufacturing a piezoelectric film type actuator according to Claim 1, wherein a porous layer is formed between the intermediate transfer member and the piezoelectric film.

13. A method for manufacturing a piezoelectric film type actuator according to Claim 12, wherein said porous layer contains metal oxide.

25

14. A piezoelectric film type actuator manufactured by the method for manufacturing a

piezoelectric film type actuator according to Claim 1.

15. A method for manufacturing a liquid discharge head provided with a base plate portion having liquid discharge ports; liquid chambers connected with said liquid discharge ports; and a piezoelectric film type actuator formed by a piezoelectric film and a oscillating plate provided for a part of said liquid chambers, for discharging liquid from the liquid discharge ports by means of the flexural oscillation of said piezoelectric film type actuator, comprising the following steps of:

forming a piezoelectric film on an intermediate transfer member;

15 bonding the piezoelectric film on said intermediate member and said oscillating plate structural member; and

peeling off said intermediate transfer member from said piezoelectric film.

20

16. A method for manufacturing a liquid discharge head according to Claim 15, wherein said piezoelectric film contains lead, titanium, and zirconium.

25 17. A method for manufacturing a liquid discharge head according to Claim 15, wherein said piezoelectric film is patterned.

18. A method for manufacturing a liquid discharge head according to Claim 15, wherein the surface roughness Ra of said piezoelectric film is 0.01 μm to 2.5 μm .

5

19. A method for manufacturing a liquid discharge head according to Claim 15, wherein in the step of bonding the piezoelectric film and the oscillating plate structural member, said piezoelectric film and said oscillating plate structural member are bonded by means of energized heating, low temperature heating, or energized contact under pressure through single metal, alloy, metal oxide, metal nitride, or metallic compound.

15

20. A method for manufacturing a liquid discharge head according to Claim 15, wherein in the step of peeling off the intermediate transfer member from the piezoelectric film, said intermediate transfer member is peeled off by the irradiation of laser beam from the intermediate transfer member side.

20

21. A method for manufacturing a liquid discharge head according to Claim 20, wherein said laser beam is excimer laser beam.

25

22. A method for manufacturing a liquid discharge

head according to Claim 20, wherein said laser beam is infrared laser beam.

23. A method for manufacturing a liquid discharge
5 head according to Claim 21, wherein the transmissivity
of 230 to 260 nm wavelength of said intermediate
transfer member is 20% or more.

24. A method for manufacturing a liquid discharge
10 head according to Claim 22, wherein the transmissivity
of 700 nm to 1,250 nm wavelength of said intermediate
transfer member is 20% or more.

25. A method for manufacturing a liquid discharge
15 head according to Claim 15, wherein in the step of
peeling off an intermediate transfer member from a
piezoelectric film, a fluid flux is discharged between
the intermediate transfer member and the piezoelectric
film to peel off said intermediate transfer member.

20

26. A method for manufacturing a liquid discharge
head according to Claim 15, wherein a porous layer is
formed between the intermediate transfer member and the
piezoelectric film.

25

27. A method for manufacturing a liquid discharge
head according to Claim 26, wherein said porous layer

contains metal oxide.

28. A liquid discharge head manufactured by the
method for manufacturing a liquid discharge head
5 according to Claim 15.

ABSTRACT OF THE DISCLOSURE

A method for manufacturing a piezoelectric film type actuator, which is provided with a piezoelectric film and an oscillating plate structural member bonded therefor, comprises the steps of forming a piezoelectric film on an intermediate transfer member; bonding the piezoelectric film on the intermediate member and the oscillating plate structural member; and peeling off the intermediate transfer member from the piezoelectric film. Through the steps thus arranged, it becomes possible to enhance the bonding strength and durability of the piezoelectric film and the oscillating plate structural member without using a bonding agent in the manufacture of a highly reliable piezoelectric film type actuator.